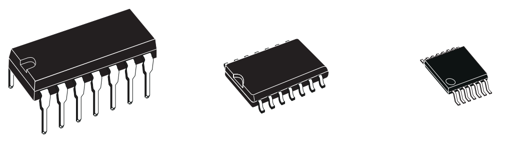
M74HCT04

HEX INVERTER

- HIGH SPEED: t_{PD} = 11ns (TYP.) at V_{CC}=4.5V
- LOW POWER DISSIPATION: I_{CC} = 1µA(MAX.) at T_A=25°C
- COMPATIBLE WITH TTL OUTPUTS : V_{IH} = 2V (MIN.) V_{IL} = 0.8V (MAX)
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL}$ = 4mA (MIN)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 04



DIP **SOP** **TSSOP**

ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT04B1R	
SOP	M74HCT04M1R	M74HCT04RM13TR
TSSOP		M74HCT04TTR

DESCRIPTION

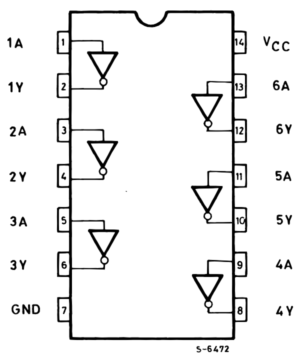
The M74HCT04 is an high speed CMOS HEX INVERTER fabricated with silicon gate C^2MOS technology.

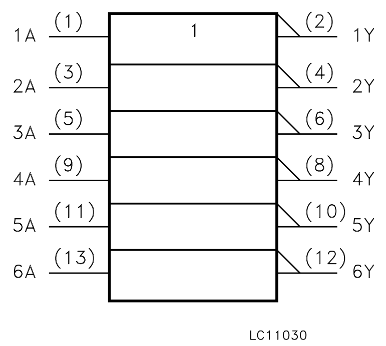
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

The M74HCT04 is designed to directly interface HSC^2MOS systems with TTL and NMOS components.

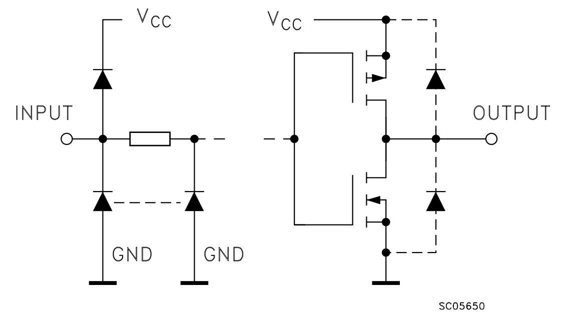
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	H
H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
t_r, t_f	Input Rise and Fall Time (V_{CC} = 4.5 to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V_{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V_{OH}	High Level Output Voltage	4.5	I_O=-20 µA	4.4	4.5		4.4		4.4		V
			I_O=-4.0 mA	4.18	4.31		4.13		4.10		
V_{OL}	Low Level Output Voltage	4.5	I_O=20 µA		0.0	0.1		0.1		0.1	V
			I_O=4.0 mA		0.17	0.26		0.33		0.40	
I_I	Input Leakage Current	5.5	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	µA
I_{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	µA
ΔI_{CC}	Additional Worst Case Supply Current	5.5	Per Input pin V_I = 0.5V or V_I = 2.4V Other Inputs at V_{CC} or GND I_O = 0			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6ns)

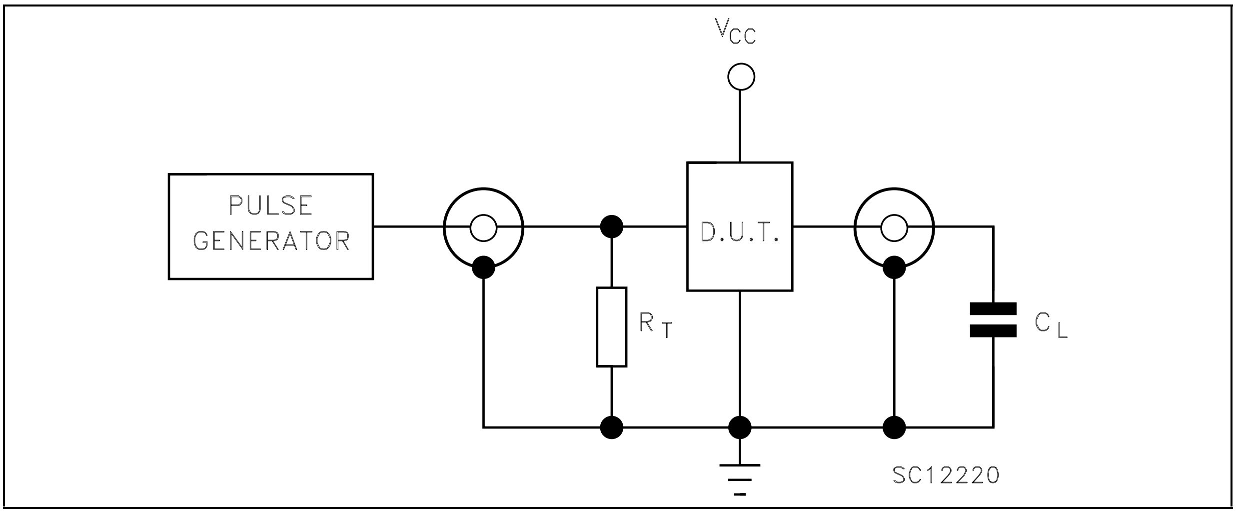
Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	4.5			8	15		19		23	ns
t_{PLH} t_{PHL}	Propagation Delay Time	4.5			11	18		23		27	ns

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (note 1)				20						pF

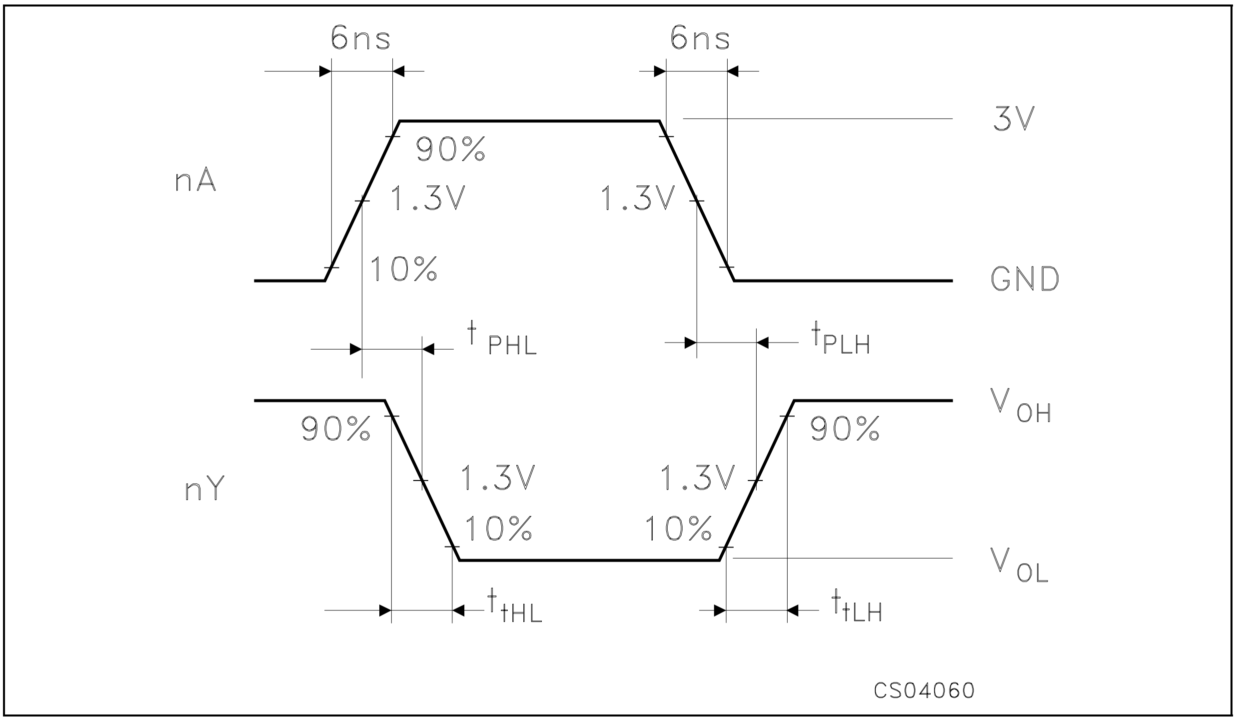
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$ (per gate)

TEST CIRCUIT



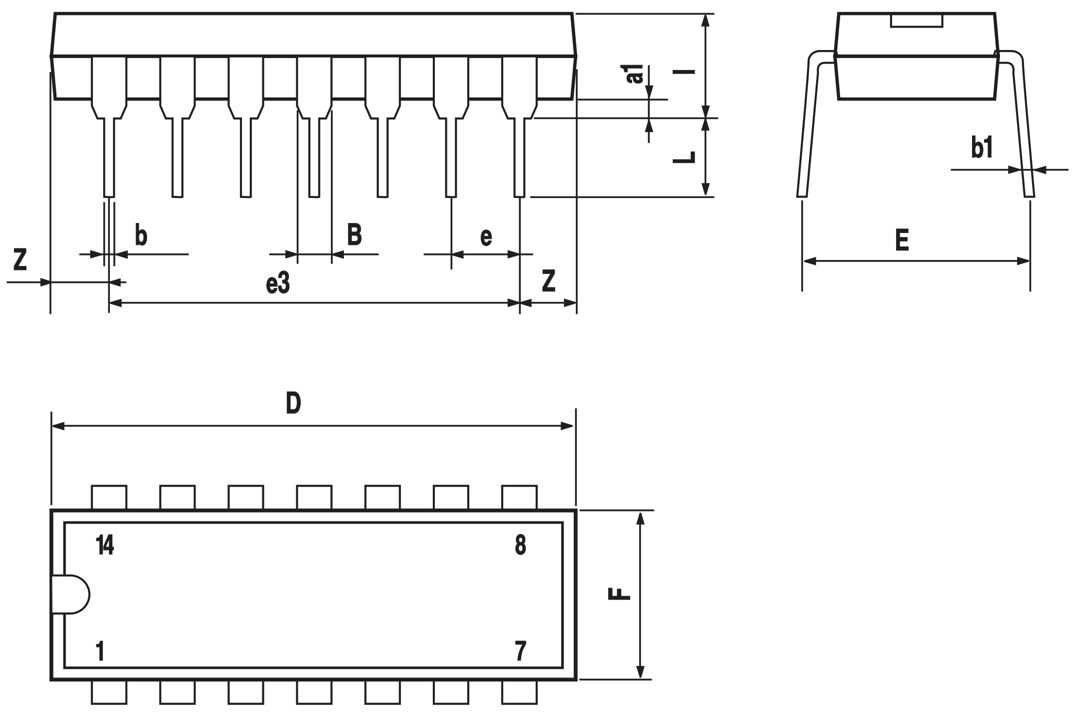
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



Plastic DIP-14 MECHANICAL DATA

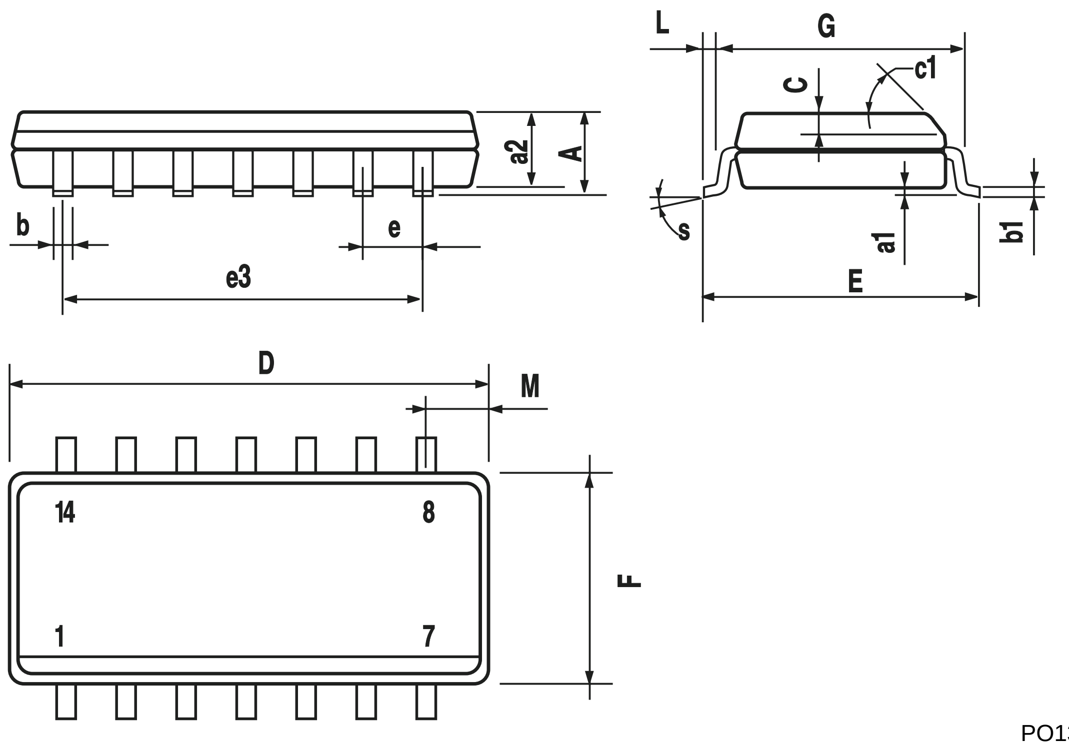
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

SO-14 MECHANICAL DATA

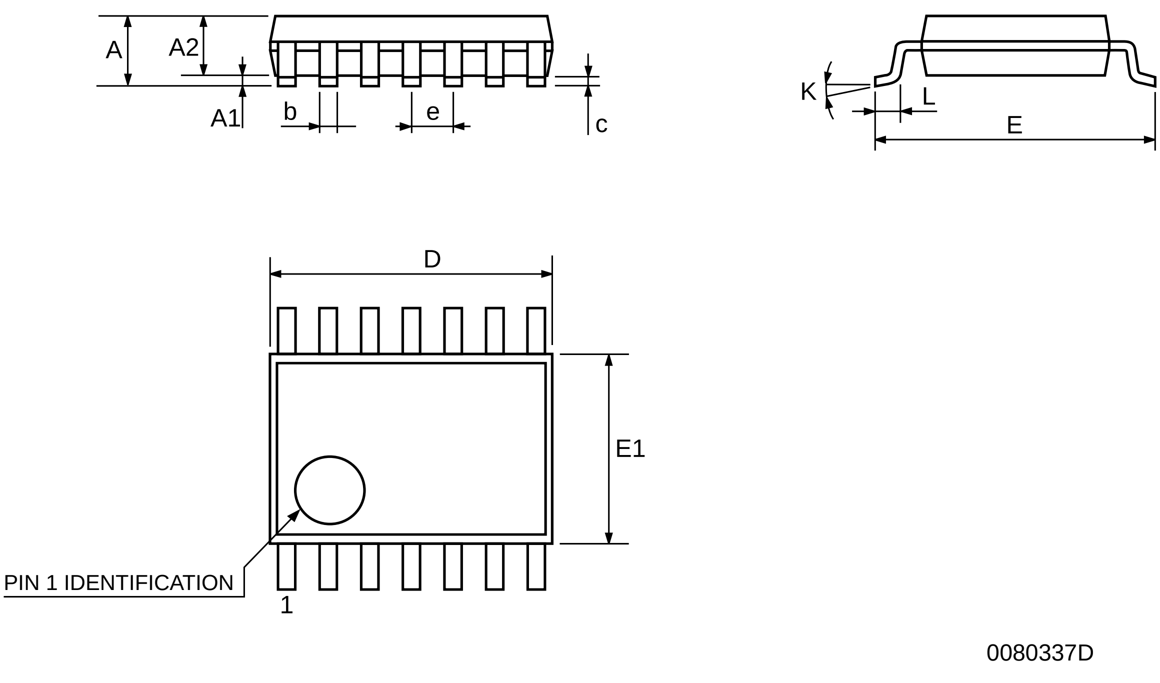
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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